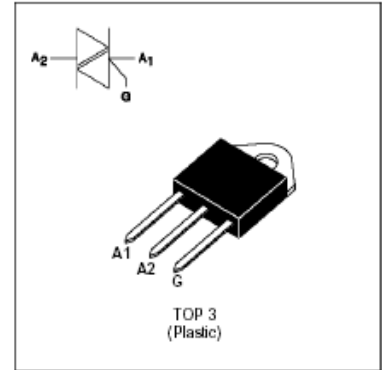


## BTA25, BTA26 (25A TRIACS)

Symbol	Value	Unit
$I_{T(RMS)}$	25	A
$V_{DRM}/V_{RRM}$	600 and 800	V
$I_{G(Q1)}$	35 to 50	mA



## ABSOLUTE RATING

Symbol	Parameter		Value	Units
$I_{T(RMS)}$	RMS on-state current (full sine wave). $T_C=90^\circ\text{C}$		25	A
	Non-repetitive peak on-state current ( $T_j=25^\circ\text{C}$ , full cycle)	F=50Hz t=20ms	250	
		F=60Hz t=16.7ms	260	
dl/dt	Critical rate of rise of on-state current $I_G=2 \times I_{GT}$ , $t_r \leq 100\text{ns}$	F=120Hz $T_j=125^\circ\text{C}$	50	A/μs
$I_{GM}$	Peak gate current	$t_p=20 \mu\text{s}$ $T_j=125^\circ\text{C}$	4	A
$P_{G(AV)}$	Average gate power dissipation $T_j=125^\circ\text{C}$		1	W
$T_{stg}$	Storage junction temperature range		-40~150	$^\circ\text{C}$
$T_j$	Operating junction temperature range		-40~150	$^\circ\text{C}$

## THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction to case	1.1	$^\circ\text{C}/\text{W}$
$R_{ti(j-a)}$	Junction to ambient	50	$^\circ\text{C}/\text{W}$

**ELECTRICAL CHARACTERISTICS (T<sub>j</sub>=25°C unless otherwise stated)**

Symbol	Testing conditions		Quadrant		Suffix			Unit
					CW	BW	B	
I <sub>GT</sub>	V <sub>D</sub> =12V, R <sub>L</sub> =33 Ω		I - II - III	Max	35	50	50	mA
			IV		-	-	100	
V <sub>GT</sub>			ALL	Max	1.3			V
V <sub>GD</sub>	V <sub>D</sub> =V <sub>DRM</sub> , R <sub>L</sub> =3.3K Ω, T <sub>j</sub> =125°C		ALL	Min	0.2			V
I <sub>L</sub>	I <sub>G</sub> =1.2I <sub>GT</sub>		I - III	Max	70	80	70	mA
			II		80	100	160	
I <sub>H</sub>	I <sub>T</sub> =500mA		ALL	Max	35	50	50	mA
V <sub>TM</sub>	I <sub>T</sub> =35A, t=380 μ s		ALL	Max	1.55			V
I <sub>DRM</sub> I <sub>RRM</sub>	V <sub>DRM</sub> =V <sub>RRM</sub>	T <sub>j</sub> =25°C		Max	5			μ A
		T <sub>j</sub> =125°C			3			mA
dv/dt	V <sub>D</sub> =67% V <sub>DRM</sub> Gate open T <sub>j</sub> =125°C			Min	500	1000	500	V/ μ s